

HY860F

ABSOLUTE MAXIMUM RATINGS AT TA=25°C

PARAMETER	MAXIMUM RATING	UNIT
IR Diode Continuous Forward Current	50	mA
IR Diode Reverse Voltage	5	V
Transistor Collector Current	20	mA
Transistor Power Dissipation	75	mW (Note 1)
IR Diode Peak Forward Current (Pulse Wide = 10 μ S, 300 pps)	1	A
Diode Power Dissipation	100	mW (Note 1)
Phototransistor Collector-Emitter Voltage	30	V
Phototransistor Emitter-Collector Voltage	5	V
Operating Temperature Range	-55°C to +100°C	
Storage Temperature Range	-55°C to +100°C	
Lead Soldering Temperature [1.6mm(.063") From Case]	260°C for 5 Seconds	

Note 1: Derate Linearly 1.33mW/°C from 25°C

NOTES:

1. All dimensions are in millimeters (inches).
2. Tolerance is $\pm 0.25\text{mm}$ (.010") unless otherwise noted.

TYPICAL ELECTRICAL / OPTICAL CHARACTERISTICS CURVES

(25°C Ambient Temperature Unless Otherwise Noted)

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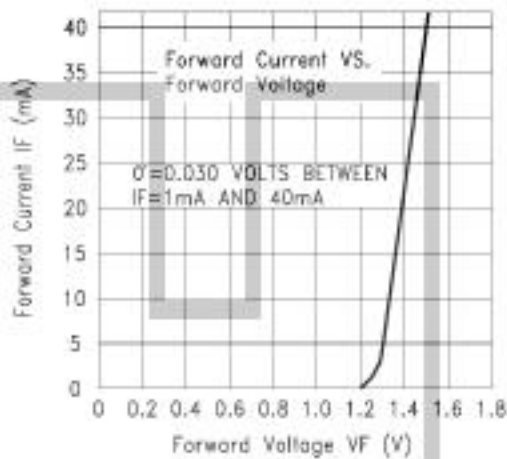


Fig. 1 FORWARD CURRENT VS. FORWARD VOLTAGE

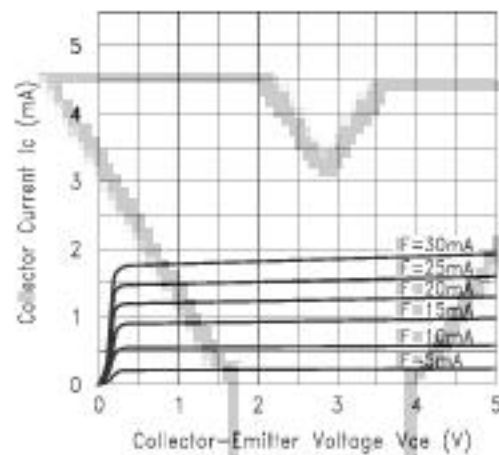


Fig. 2 COLLECTOR CURRENT VS. COLLECTOR VOLTAGE

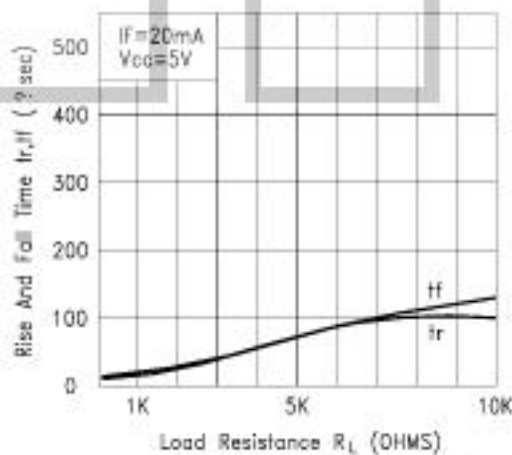


Fig. 3 RISE AND FALL TIME VS. LOAD RESISTANCE

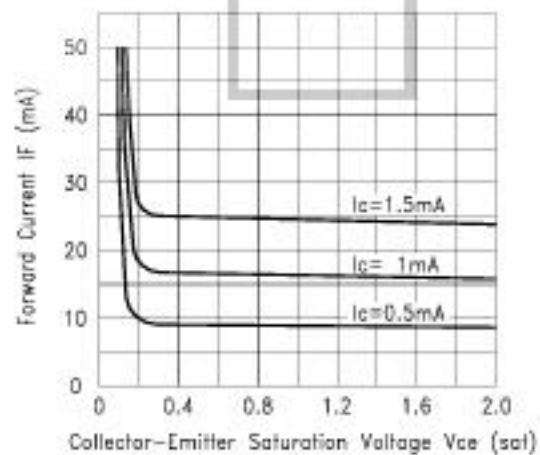


Fig. 4 FORWARD CURRENT VS. COLLECTOR-EMITTER SATURATION VOLTAGE

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ELECTRICAL OPTICAL CHARACTERISTICS AT TA=25°C

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
INPUT LED						
Forward Voltage	V _F		1.2	1.6	V	I _F = 20mA
Reverse Current	I _R			100	μA	V _R = 5V
OUTPUT PHOTOTRANSISTOR						
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	30			V	I _C = 1mA
Emitter-Collector Breakdown Voltage	V _{(BR)ECO}	5			V	I _E = 100 μA
Collector-Emitter Dark Current	I _{CEO}			100	nA	V _{CE} = 10V
COUPLER						
Collector-Emitter Saturation Voltage	V _{CE(SAT)}			0.4	V	I _C = 0.2mA I _F = 20mA
On State Collector Current	I _{c(ON)}	0.4		2.4	mA	V _{CE} = 5V I _F = 20mA

NOTES:

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